TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

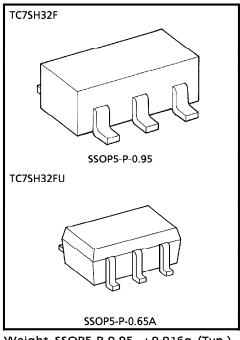
# TC7SH32F, TC7SH32FU

## 2-INPUT OR GATE

The TC7SH32 is an advanced high speed CMOS 2-INPUT OR GATE fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation. The internal circuit is composed of 4 stages including buffer output, which provide high noise immunity and stable output. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatchedsupply and input voltages.

## **FEATURES**

- High Speed  $\cdots$   $t_{pd} = 3.8$ ns (Typ.) at  $V_{CC} = 5V$
- Low Power Dissipation ..................................  $I_{CC} = 2\mu A$  (Max.) at
- High Noise Immunity ················ V<sub>NIH</sub> = V<sub>NIL</sub>
   = 28% V<sub>CC</sub> (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays ······· t<sub>pLH</sub>≒t<sub>pHL</sub>
- Wide Operating Voltage Range····· V<sub>CC</sub> (opr) = 2~5.5V

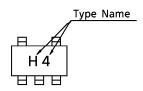


Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

#### **MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	Vcc	-0.5~7.0	V
DC Input Voltage	VIN	-0.5~7.0	٧
DC Output Voltage	Vout	-0.5~V <sub>CC</sub> +0.5	V
Input Diode Current	ΙΚ	- 20	mA
Output Diode Current	<sup>I</sup> ОК	± 20	mA
DC Output Current	IOUT	± 25	mA
DC V <sub>CC</sub> /Ground Current	Icc	± 50	mA
Power Dissipation	PD	200	mW
Storage Temperature	T <sub>stg</sub>	<b>-65∼150</b>	°C
Lead Temperature (10s)	TL	260	°C

#### MARKING



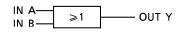
TRUTH TABLE

А	В	Υ
Н	Н	Н
L	Н	Н
Н	L	Н
L	L	L

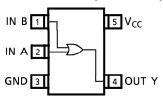
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## **LOGIC DIAGRAM**



## PIN ASSIGNMENT (TOP VIEW)



#### **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT	
Supply Voltage	Vcc	2.0~5.5	V	
Input Voltage	VIN	0~5.5	٧	
Output Voltage	Vout	0~V <sub>CC</sub>	٧	
Operating Temperature	T <sub>opr</sub>	<b>- 40∼85</b>	°C	
Input Disc and Fall Time	ا ا ما	$0 \sim 100 \text{ (V}_{CC} = 3.3 \pm 0.3 \text{V)}$	/ \ /	
Input Rise and Fall Time	d <sub>t</sub> /d <sub>v</sub>	$0\sim 20 \ (V_{CC} = 5 \pm 0.5V)$	ns / V	

## DC ELECTRICAL CHARACTERISTICS

DADAMETER	CVMPOL	TEST	TEST CONDITION VCC		Ta = 25°C			Ta = − 40~85°C		LINUT	
PARAMETER	SYMBOL	CIR- CUIT			Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High Lovel Instit						1.50	_	_	1.50	_	
High-Level Input Voltage	VIH	<u> </u>	_		3.0~	Vcc		<u> </u>	Vcc		V
Voltage					5.5	×0.7			×0.7	_	
Low-Level Input					2.0	_	_	0.50	_	0.50	
Voltage	V <sub>IL</sub>	_		_	3.0~ 5.5			Vcc		VCC	V
Voltage								×0.3		×0.3	
			V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>		2.0	1.9	2.0	—	1.9	<b>—</b>	
High Level		_		$I_{OH} = -50\mu A$	3.0	2.9	3.0	—	2.9	_	_ v   _ v
Output-Voltage	Voн				4.5	4.4	4.5		4.4	_	
Output-voltage				$I_{OH} = -4mA$	3.0	2.58	_	—	2.48	<u> </u>	
				$I_{OH} = -8mA$	4.5	3.94	_	—	3.80	_	
					2.0	_	0.0	0.1	_	0.1	
Low Lovel				$I_{OL} = 50 \mu A$	3.0	_	0.0	0.1		0.1	
Low-Level Output-Voltage	VOL	— V <sub>IN</sub> = V <sub>II</sub>	V <sub>IN</sub> = V <sub>IL</sub>		4.5	_	0.0	0.1		0.1	V
				$I_{OL} = 4mA$	3.0	_	_	0.36	_	0.44	
				$I_{OL} = 8mA$	4.5	_	_	0.36	<u> </u>	0.44	
Input Leakage Current	IN	_	V <sub>IN</sub> = 5.5V or GND		0~ 5.5	_	_	± 0.1	_	± 1.0	
Quiescent Supply Current	lcc	_	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5			2.0		20.0	μΑ

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# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$ )

PARAMETER SYMBOL	TEST	TEST CONDITION			Ta = 25°C			Ta = − 40~85°C		UNIT	
	CIR- CUIT		V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	MIN.	TYP.	MAX.	MIN.	MAX.		
				3.3 ± 0.3	15	_	5.5	7.9	1.0	9.5	ns
	t <sub>PLH</sub>	ı	_		50	_	8.0	11.4	1.0	13.0	
	tPHL			5.0 ± 0.5	15	_	3.8	5.5	1.0	6.5	
					50	_	5.3	7.5	1.0	8.5	
Input Capacitance	CIN	_	<del>_</del>			_	4	10	_	10	
Power Dissipation Capacitance	C <sub>PD</sub>	_	Note (1)			_	15		_		pF

Note (1): CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

| CC (opr) = CpD·VCC·fIN + ICC

# INPUT EQUIVALENT CIRCUIT

